

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Amit S. Kelkar et al. PATENT APPLICATION  
Serial No.: 09/650,961 Group Art Unit: 2825  
Filed: August 29, 2000 Examiner: C.P. Lytle  
For: METHOD OF FORMING PRE-METAL DIELECTRIC FILM  
ON A SEMICONDUCTOR SUBSTRATE INCLUDING FIRST  
LAYER OF UNDOPED OXIDE OF HIGH OZONE:TEOS  
VOLUME RATIO AND SECOND LAYER OF LOW OZONE  
DOPED BPSG

Preliminary Amendment

Commissioner for Patents  
Alexandria, VA 22313-1450

Sir:

Applicant submits this Preliminary Amendment of the  
above-identified application submitted for reissue herewith.  
A Version With Markings to Show Changes Made is attached.

In the claims:

Please amend claims 10, 11 and 13 as follows:

10. (amended) The method of claim 8, wherein the heat  
treatment is carried out at a temperature of less than 800° C.

11. (amended) The method of claim 8 wherein the  
semiconductor substrate has a plurality of polysilicon  
conductors on a top surface thereof and wherein the second  
layer of film is planarized to be of a thickness of at least  
200 nm above the polysilicon conductors.